

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Canceled)
2. (Previously Presented) A portable phone comprising:  
a body;  
a semiconductor device contained in the body, said semiconductor device comprising:  
a substrate;  
a passive component including at least an inductor formed over the substrate;  
an insulating film covering said passive component;  
an insulation layer attached to said insulating film via an adhesive;  
a circuit including at least one thin film transistor formed over said insulation layer,  
wherein said circuit is electrically connected to said passive component by at least one electrode through an opening of said insulation layer.
3. (Previously Presented) The portable phone according to claim 2 wherein said substrate is a quartz substrate.
4. (Previously Presented) The portable phone according to claim 2 wherein said insulation layer comprises aluminum nitride.
5. (Previously Presented) A portable phone comprising:  
a substrate;

a passive component including at least a capacitor formed over the substrate;  
an insulating film covering said passive component;  
an insulation layer attached to said insulating film via an adhesive;  
a circuit including at least one thin film transistor formed over said insulation layer,  
wherein said circuit is electrically connected to said passive component by at least one  
electrode through an opening of said insulation layer.

6. (Previously Presented) The portable phone according to claim 5 wherein said substrate  
is a quartz substrate.

7. (Previously Presented) The portable phone according to claim 5 wherein said  
insulation layer comprises aluminum nitride.

8. (Previously Presented) A portable phone comprising:

a body; and

a semiconductor device contained in the body, said semiconductor device comprising:

a substrate;

a passive component including at least a SAW filter formed over the substrate;

an insulating film covering said passive component;

an insulation layer attached to said insulating film via an adhesive;

a circuit including at least one thin film transistor formed over said insulation  
layer,

wherein said circuit is electrically connected to said passive component by at least  
one electrode through an opening of said insulation layer.

9. (Previously Presented) The portable phone according to claim 8 wherein said substrate  
is a quartz substrate.

10. (Previously Presented) The portable phone according to claim 8 wherein said layer comprises aluminum nitride.

11. (Previously Presented) A portable phone comprising:  
a body; and  
a semiconductor device contained in the body, said semiconductor device comprising:  
a substrate;  
a passive component including at least a band-pass filter formed over the substrate;  
an insulating film covering said passive component;  
an insulation layer attached to said insulating film via an adhesive;  
a circuit including at least one thin film transistor formed over said insulation layer,  
wherein said circuit is electrically connected to said passive component by at least one electrode through an opening of said insulation layer.

12. (Previously Presented) The portable phone according to claim 11 wherein said substrate is a quartz substrate.

13. (Previously Presented) The portable phone according to claim 11 wherein said layer comprises aluminum nitride.

14. (Previously Presented) A portable phone comprising:  
a body; and  
a semiconductor device contained in the body, said semiconductor device comprising:  
a substrate;  
an oscillating component formed over the substrate;  
an insulating film covering said oscillating component;

an insulation layer attached to said insulating film via an adhesive;  
a circuit including at least one thin film transistor formed over said insulation layer,  
wherein said circuit is electrically connected to said oscillating component by at least one electrode through an opening of said insulation layer.

15. (Previously Presented) The portable phone according to claim 14 wherein said substrate is a quartz substrate.

16. (Previously Presented) The portable phone according to claim 14 wherein said layer comprises aluminum nitride.

17-20. (Canceled)

21. (New) A semiconductor device capable of operating with a radio frequency, said semiconductor device comprising:

a substrate;  
a passive component including at least an inductor formed over the substrate;  
an insulating film covering said passive component;  
an insulation layer attached to said insulating film via an adhesive; and  
a circuit including at least one thin film transistor formed over said insulation layer,  
wherein said circuit is electrically connected to said passive component by at least one electrode through an opening of said insulation layer.

22. (New) The semiconductor device according to claim 21 wherein said substrate is a ceramic substrate.

23. (New) The semiconductor device according to claim 21 wherein said insulation layer comprises aluminum nitride.

24. (New) A semiconductor device capable of operating with a radio frequency, said semiconductor device comprising:

- a substrate;
- a passive component including at least a capacitor formed over the substrate;
- an insulating film covering said passive component;
- an insulation layer attached to said insulating film via an adhesive; and
- a circuit including at least one thin film transistor formed over said insulation layer, wherein said circuit is electrically connected to said passive component by at least one electrode through an opening of said insulation layer.

25. (New) The semiconductor device according to claim 24 wherein said substrate is a ceramic substrate.

26. (New) The semiconductor device according to claim 24 wherein said insulation layer comprises aluminum nitride.

27. (New) A semiconductor device capable of operating with a radio frequency, said semiconductor device comprising:

- a substrate;
- a passive component including at least a SAW filter formed over the substrate;
- an insulating film covering said passive component;
- an insulation layer attached to said insulating film via an adhesive; and
- a circuit including at least one thin film transistor formed over said insulation layer, wherein said circuit is electrically connected to said passive component by at least one electrode through an opening of said insulation layer.

28. (New) The semiconductor device according to claim 27 wherein said substrate is a ceramic substrate.

29. (New) The semiconductor device according to claim 27 wherein said layer comprises aluminum nitride.

30. (New) A semiconductor device capable of operating with a radio frequency, said semiconductor device comprising:

- a substrate;
- a passive component including at least a band-pass filter formed over the substrate;
- an insulating film covering said passive component;
- an insulation layer attached to said insulating film via an adhesive; and
- a circuit including at least one thin film transistor formed over said insulation layer, wherein said circuit is electrically connected to said passive component by at least one electrode through an opening of said insulation layer.

31. (New) The semiconductor device according to claim 30 wherein said substrate is a ceramic substrate.

32. (New) The semiconductor device according to claim 30 wherein said layer comprises aluminum nitride.

33. (New) A semiconductor device capable of operating with a radio frequency, said semiconductor device comprising:

- a substrate;
- an oscillating component formed over the substrate;
- an insulating film covering said oscillating component;

an insulation layer attached to said insulating film via an adhesive; and  
a circuit including at least one thin film transistor formed over said insulation layer,  
wherein said circuit is electrically connected to said passive component by at least one  
electrode through an opening of said insulation layer.

34. (New) The semiconductor device according to claim 33 wherein said substrate is a  
ceramic substrate.

35. (New) The semiconductor device according to claim 33 wherein said layer comprises  
aluminum nitride.

36. (New) The semiconductor device according to claim 21 wherein said semiconductor  
device is a mobile phone.

37. (New) The semiconductor device according to claim 24 wherein said semiconductor  
device is a mobile phone.

38. (New) The semiconductor device according to claim 27 wherein said semiconductor  
device is a mobile phone.

39. (New) The semiconductor device according to claim 30 wherein said semiconductor  
device is a mobile phone.

40. (New) The semiconductor device according to claim 33 wherein said semiconductor  
device is a mobile phone.

41. (New) The semiconductor device according to claim 21 wherein said semiconductor  
device is a portable intelligent terminal.

42. (New) The semiconductor device according to claim 24 wherein said semiconductor device is a portable intelligent terminal.

43. (New) The semiconductor device according to claim 27 wherein said semiconductor device is a portable intelligent terminal.

44. (New) The semiconductor device according to claim 30 wherein said semiconductor device is a portable intelligent terminal.

45. (New) The semiconductor device according to claim 33 wherein said semiconductor device is a portable intelligent terminal.